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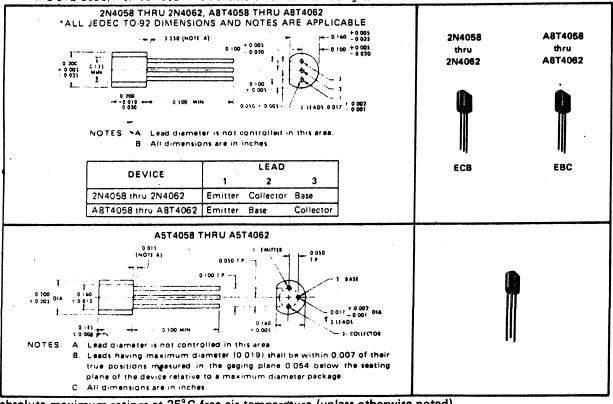
TYPES 2N4058 THRU 2N4062, A5T4058 THRU A5T4062, A8T4058 THRU A8T4062 P-N-P SILICON TRANSISTORS BULLETIN NO. DL-S 7311962, MARCH 1973

SILECT TRANSISTORS

- Ideal for Low-Level Amplifier Applications
- Rugged One-Piece Construction with In-Line Leads or Standard TO-18 100-mil Pin-Circle Configuration
- Recommended for Complementary Use with 2N3707 thru 2N3711, A5T3707 thru A5T3711, or A8T3707 thru A8T3711

mechanical data

These transistors are encapsulated in a plastic compound specifically designed for this purpose, using a highly mechanized process developed by Texas Instruments. The case will withstand soldering temperatures without deformation. These devices exhibit stable characteristics under high-humidity conditions and are capable of meeting MIL-STD-202C, Method 106B. The transistors are insensitive to light.



absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Collector Base Voltage				٠.																		,			-30 V
Collector Emitter Voltage (See No	te 1)																			,				-30 V
Emitter-Base Voltage																	•								-6 V
Continuous Collector Current																								_	-30 mA
Continuous Device Dissipation at ((or b	elo	w)	25°	,c	Fre	e-A	۱ir	Te	m	per	rati	ure	(5	ee	No	ote	2)				<	{ 6	325 mW 360 mW
Storage Temperature Range Lead Temperature 1/16 Inch from																									
Lead Temperature 1/16 Inch from	Cas	e to	rı	U 5	ecc	วทส	S																		20U L

NOTES: 1. This value applies when the base-emitter diode is open-circuited.

2. Derate the 625-mW rating linearly to 150°C free-air temperature at the rate of 5 mW/°C. Derate the 360-mW (JEDEC registered) rating linearly to 150°C free-air temperature at the rate of 2.88 mW/°C.

^{*}The asterisk identifies JEDEC registered data for the 2N4058 through 2N4062 only. This data sheet contains all applicable registered data in effect at the time of publication.